

# MBR2020 THRU MBR20100

## Features

- Metal of siliconrectifier, majonty carrier conducton
- Guard ring for transient protection
- Low power loss high efficiency
- High surge capacity, High current capability

## Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C

Microsemi Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBR2020	MBR2020	20V	14V	20V
MBR2030	MBR2030	30V	21V	30V
MBR2035	MBR2035	35V	24.5V	35V
MBR2040	MBR2040	40V	28V	40V
MBR2045	MBR2045	45V	31.5V	45V
MBR2060	MBR2060	60V	42V	60V
MBR2080	MBR2080	80V	56V	80V
MBR20100	MBR20100	100V	70V	100V

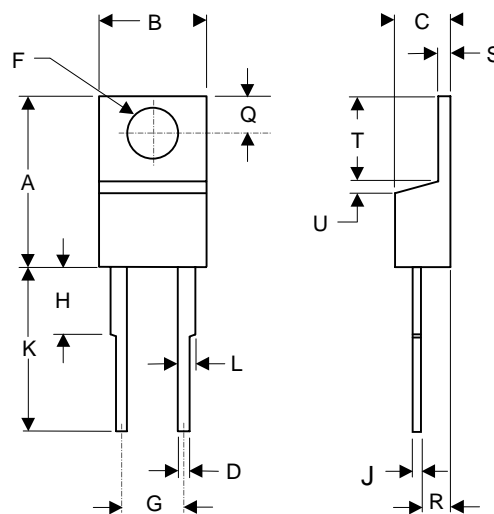
## Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	20A	$T_C = 135^\circ\text{C}$
Peak Forward Surge Current	$I_{FSM}$	150A	8.3ms, half sine
Maximum Forward Voltage Drop Per Element MBR2020-2045 MBR2060 MBR2080-20100	$V_F$	.63V .75V .84V	$I_{FM} = 20\text{A per element};$ $T_A = 25^\circ\text{C}^*$
Maximum DC Reverse Current At Rated DC Blocking Voltage	IR	0.1mA	$T_J = 25^\circ\text{C}$

\*Pulse test: Pulse width 300  $\mu\text{sec}$ , Duty cycle 1%

## 20 Amp Schottky Barrier Rectifier 20 to 100 Volts

### TO-220AC



DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.595	.620	15.11	15.75	
B	.380	.405	9.65	10.29	
C	.160	.190	4.06	4.82	
D	.025	.035	0.64	0.89	
F	.142	.147	3.61	3.73	
G	.190	.210	4.83	5.33	
H	.110	.130	2.79	3.30	
J	.018	.025	0.46	0.64	
K	.500	.562	12.70	14.27	
L	.045	.060	1.14	1.52	
Q	.100	.120	2.54	3.04	
R	.080	.110	2.04	2.79	
S	.045	.055	1.14	1.39	
T	.235	.255	5.97	6.48	
U	-----	.050	-----	1.27	